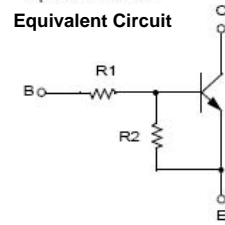
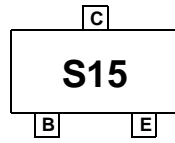
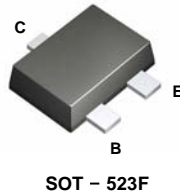


# FJY3015R

## NPN Epitaxial Silicon Transistor

### Features

- Switching circuit, Inverter, Interface circuit, Driver Circuit
- Built in bias Resistor (R1=2.2KΩ, R2=10KΩ)



### Absolute Maximum Ratings\* $T_a = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Value	Units
$V_{CBO}$	Collector-Base Voltage	50	V
$V_{CEO}$	Collector-Emitter Voltage	50	V
$V_{EBO}$	Emitter-Base Voltage	10	V
$I_C$	Collector Current	100	mA
$T_{STG}$	Storage Temperature Range	-55~150	$^\circ\text{C}$
$T_J$	Junction Temperature	150	$^\circ\text{C}$
$P_C$	Collector Power Dissipation, by $R_{\theta JA}$	N/A	mW

\* These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

### Thermal Characteristics\* $T_a = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Max	Units
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	N/A	$^\circ\text{C}/\text{W}$

\* Minimum land pad.

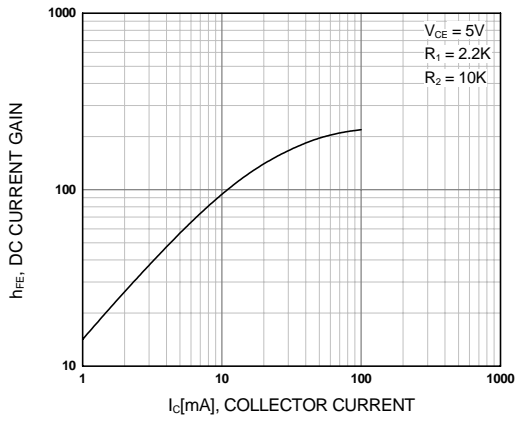
### Electrical Characteristics\* $T_C = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Condition	MIN	Typ	MAX	Units
$V_{(BR)CBO}$	Collector-Base Breakdown Voltage	$I_C = 10 \mu\text{A}, I_E = 0$	50			V
$V_{(BR)CEO}$	Collector-Base Breakdown Voltage	$I_C = 100 \mu\text{A}, I_B = 0$	50			V
$I_{CBO}$	Collector-Cutoff Current	$V_{CB} = 40 \text{V}, I_E = 0$			0.1	$\mu\text{A}$
$h_{FE}$	DC Current Gain	$V_{CE} = 5 \text{V}, I_C = 10 \text{mA}$	33			
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C = 10 \text{mA}, I_B = 0.5 \text{mA}$			0.3	V
$f_T$	Current Gain - Bandwidth Product	$V_{CE} = 10\text{V}, I_C = 5 \text{mA}$		250		MHz
$C_{cb}$	Output Capacitance	$V_{CB} = 10 \text{V}, I_E = 0, f = 1.0 \text{MHz}$		3.7		pF
$V_{I(off)}$	Input Off Voltage	$V_{CE} = 5 \text{V}, I_C = 100\mu\text{A}$	0.3			V
$V_{I(on)}$	Input On Voltage	$V_{CE} = 0.3\text{V}, I_C = 20\text{mA}$			3	V
$R_1$	Input Resistor		1.5	2.2	2.9	KΩ
$R_1/R_2$	Resistor Ratio		0.20	0.22	0.25	

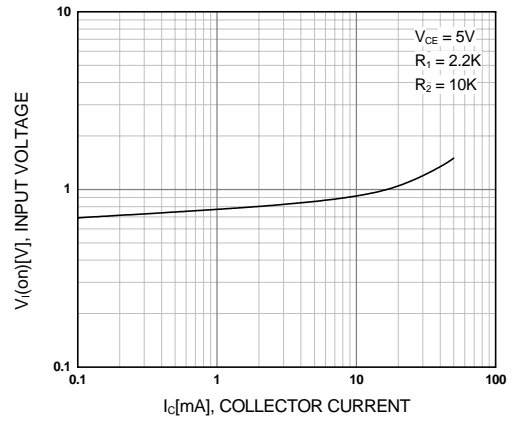
\* Pulse Test:  $PW \leq 300\mu\text{s}$ , Duty Cycle  $\leq 2\%$

## Typical Performance Characteristics

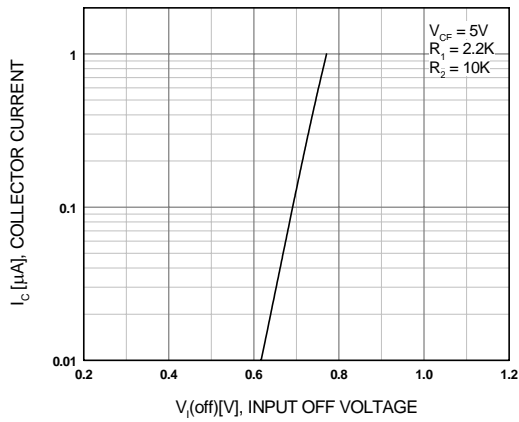
**Figure 1. DC current Gain**



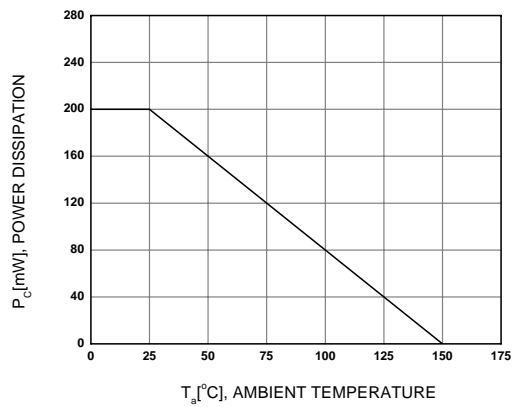
**Figure 2. Input On Voltage**



**Figure 3. Input off Voltage**

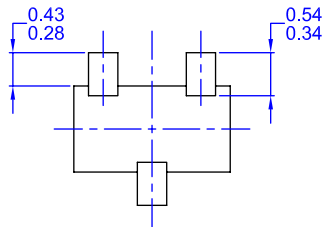
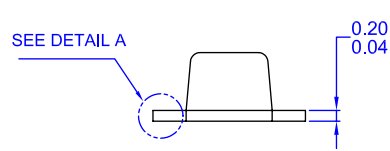
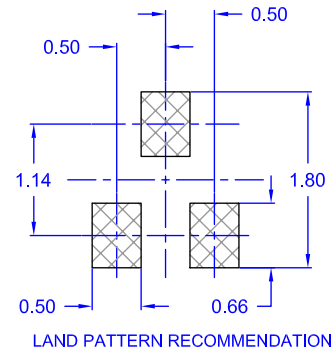
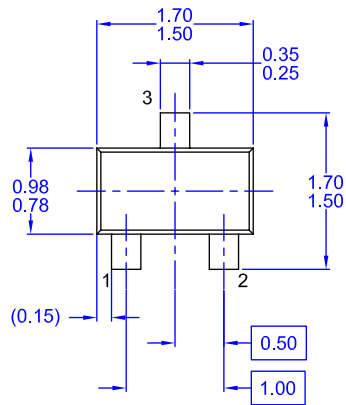


**Figure 4. Power Derating**



# Package Dimensions

## SOT-523F



- NOTES: UNLESS OTHERWISE SPECIFIED  
 A) THIS PACKAGE CONFORMS TO EIAJ SC89 PACKAGING STANDARD.  
 B) ALL DIMENSIONS ARE IN MILLIMETERS.  
 C) DIMENSIONS ARE EXCLUSIVE OF BURRS, MOLD FLASH, AND TIE BAR EXTRUSIONS.

Dimensions in Millimeters



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E <sup>2</sup> CMOS™	MSXPro™	SMART START™	VCX™
EcoSPARK®	OCX™	SPM®	Wire™
EnSigna™	OCXPro™	STEALTH™	
FACT Quiet Series™	OPTOLOGIC®	SuperFET™	
FACT®	OPTOPLANAR®	SuperSOT™-3	
FAST®	PACMAN™	SuperSOT™-6	
FASTr™	PDP-SPM™	SuperSOT™-8	
FPS™	POP™	SyncFET™	
FRFET®	Power220®	TCM™	
GlobalOptoisolator™	Power247®	The Power Franchise®	
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